

TP-98-5401  
MEMC 2340.1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent of MEMC Electronic Materials, Inc.

Patent No. 6,858,307

Issued February 22, 2005

For METHOD FOR THE PRODUCTION OF LOW DEFECT DENSITY SILICON

January 8, 2007

**LETTER TO THE PATENT AND TRADEMARK OFFICE**

TO THE COMMISSIONER FOR PATENTS,

SIR:

The above-identified patent should read at the places indicated as follows:

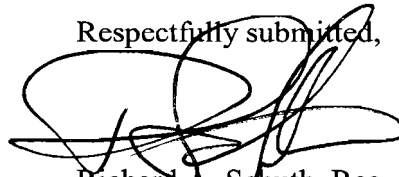
Claim 6 should have been removed from the claim set during prosecution, as it was indicated as "cancelled" in Amendment A, dated October 13, 2003.

**REMARKS**

The claims of Patent No. 6,858,307 have been compared with the file of applicant's counsel.

It is requested that the instant letter be placed in the file of Patent No. 6,858,307 for the purpose of calling attention to immaterial typographical errors in the printed patent, the correction of which should be apparent. This letter is being filed to avoid burdening the Patent and Trademark Office with a request for a formal certificate of correction.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Richard A. Schuth', is written over the typed name.

Richard A. Schuth, Reg. No. 47,929  
SENNIGER POWERS  
One Metropolitan Square, 16th Floor  
St. Louis, Missouri 63102  
(314) 231-5400